

# **isc Silicon NPN Power Transistor**

BDY77

#### **DESCRIPTION**

- · Collector-Emitter Breakdown Voltage-
  - : V<sub>(BR)CEO</sub>= 120V (Min)
- · Low Collector-Emitter Saturation Voltage
- · Excellent Safe Operating Area
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

#### **APPLICATIONS**

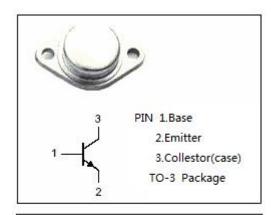
 Designed for high power audio, disk head positioners, linear amplifiers, switching regulators, solenoid drivers, and DC-DC converters or inverters.

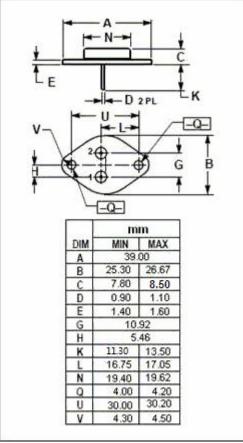
### ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>CBO</sub>	Collector-Base Voltage	150	V
V <sub>CEO</sub>	Collector-Emitter Voltage	120	٧
$V_{EBO}$	Emitter-Base Voltage	7	V
Ic	Collector Current-Continuous	16	Α
Ісм	Collector Current-Peak	30	Α
l <sub>Β</sub>	Base Current-Continuous	4	Α
Pc	Collector Power Dissipation @T <sub>C</sub> =25℃		W
TJ	Junction Temperature	150	$^{\circ}$
T <sub>stg</sub>	Storage Temperature	-65~150	${\mathbb C}$

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R <sub>th j-c</sub>	Thermal Resistance, Junction to Case	1.17	°C/W







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#### **ELECTRICAL CHARACTERISTICS**

T<sub>c</sub>=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 50mA ; I <sub>B</sub> = 0	120		V
V <sub>CE(sat)-1</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 8A; I <sub>B</sub> = 0.8A		1.0	V
V <sub>CE(sat)-2</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 16A; I <sub>B</sub> = 3.2A		2.5	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	Ic= 8A ; Vc= 2V		2.0	V
I <sub>CEO</sub>	Collector Cutoff Current	V <sub>CE</sub> = 120V; I <sub>B</sub> = 0		0.5	mA
I <sub>CEX</sub>	Collector Cutoff Current	V <sub>CE</sub> = 150V; V <sub>BE(off)</sub> = 1.5V		2.0	mA
Ісво	Collector Cutoff Current	V <sub>CB</sub> = 150V; I <sub>E</sub> = 0		0.2	mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 7V; I <sub>C</sub> = 0		0.1	mA
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 8A; V <sub>CE</sub> = 4V	40	120	
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 16A ; V <sub>CE</sub> = 4V	10		

#### **NOTICE:**

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